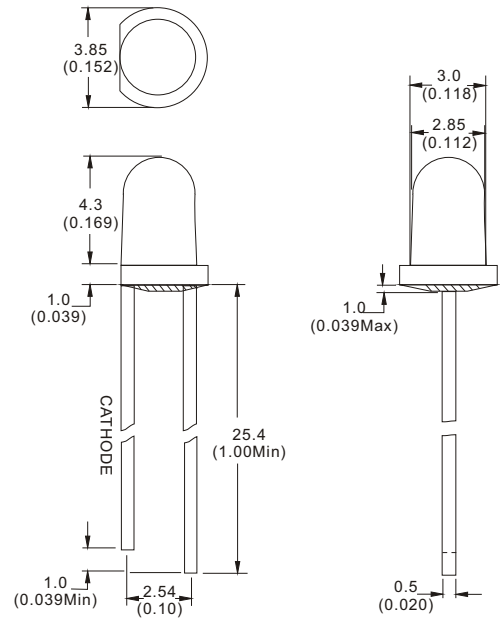




● Features:

- 1. Chip material: Silicon
- 2. Emitting color: Photo Diode
- 3. Lens Appearance: Black
- 4. Long life-solid state reliability
- 5. IC compatible/Low current capability
- 6. RoHS compliant

● Package dimensions



Notes:

- 1. All dimensions are in millimeters (inches).
- 2. Tolerance is $\pm 0.25\text{mm}$ ($0.01''$) unless otherwise specified.
- 3. An epoxy meniscus may extend about 1.0mm down to the lead.
- 4. Specifications are subject to change without notice.

● Absolute maximum ratings ($T_a = 25^\circ\text{C}$)

| Characteristic | Test Condition | Symbol | P | Units |
|----------------------------|------------------------------------|-----------|------------|------------------|
| Reverse Breakdown Voltage | | V_{BR} | 60 | V |
| Power Dissipation | | P_D | 100 | mW |
| Operating Temperature | | T_{OPR} | -40 to +80 | $^\circ\text{C}$ |
| Storage Temperature | | T_{STG} | -40 to +85 | $^\circ\text{C}$ |
| Lead Soldering Temperature | 1.60mm from body maximum 3 seconds | T_{SOL} | 260 | $^\circ\text{C}$ |



● Electrical And Optical Characteristics(Ta=25°C)

| Parameter | Test Condition | Symbol | Min. | Typ. | Max. | Units |
|---------------------------|---|----------------------------------|------|------|------|-------|
| Light Current | V _R =5V H=5mw/cm ² @940nm | I _L | --- | 80 | --- | μA |
| Reverse Dark Current | V _R =10V H=0mw/cm ² | I _D | --- | --- | 30 | nA |
| Short Circuit Current | V _R =0V H=5mw/cm ² @940nm | I _{sc} | 50 | --- | --- | μA |
| Reverse Breakdown Voltage | I _R =100uA H=0mw/cm ² | V _{BR} | 35 | --- | --- | V |
| Open Circuit Voltage | V _R =0V H=5mw/cm ² @940nm | V _{oc} | --- | 0.4 | --- | V |
| Peak Sensing Wavelength | | λ _p | --- | 940 | --- | nm |
| Rise Time Fall Time | R _L =50 Ω V _R =20V λ=850nm | t _r t _f | --- | 10 | --- | ns |
| Junction Capacitance | V _R =5V H=0mw/cm ² f=1.0MHZ | C _J | --- | 5.0 | --- | PF |
| Viewing Angle | | 2θ _½ | --- | 50 | --- | deg. |